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SHEET 1 OF 2

FORM PTO-1449	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.076DV1	APPLICATION NO. 10/033,656
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Li	#14
		FILING DATE 12/27/01	GROUP 2822

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
J.B.	4,502,914	3/5/85	Trumpp			
J.B.	5,217,926	6/8/93	Langley			
J.B.	5,219,613	6/15/93	Fabry et al.			
J.B.	5,270,267	12/14/93	Quellet			
J.B.	5,314,724	5/24/94	Tsukune et al.			
J.B.	5,376,591	12/27/94	Maeda et al.			
J.B.	5,429,995	7/4/95	Nishiyama et al.			
J.B.	5,541,445	7/30/96	Quellet			
J.B.	5,702,976	12/30/97	Schuegraf et al.			
J.B.	5,786,039	7/28/98	Brouquet			
J.B.	5,800,877	9/1/98	Maeda et al.			
J.B.	5,817,549	10/6/98	Yamazaki et al.			
J.B.	5,858,880	1/12/99	Dobson et al.			
J.B.	5,874,367	2/23/99	Dobson			
J.B.	6,001,741	12/14/99	Alers			
J.B.	6,072,227	6/6/00	Yau et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER _____ DATE CONSIDERED _____

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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SHEET 2 OF 2

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.076DV1	APPLICATION NO. 10/033,656
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Li	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE N/A	GROUP N/A 2822

*Q I P E JCB
FEB 11 2002
PATENT & TRADEMARK OFFICE*

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
J.B.	K. Beekmann et al., "Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology," presented at ULSI Conference, Portland, Oregon, October 1995, pp. 1-7 (Electrotech Ltd.)
J.B.	Joubert et al., "Plasma polymerized all-dry resist process for 0.25 µm photolithography," J. Vac. Sci. Technol. B., Vol. 12, No. 6, pp. 3909-3913, Nov./Dec. 1994.
J.B.	A. Kiermasz et al., "Planarisation for Sub-Micron Devices Utilising a New Chemistry," presented at DUMIC Conference, California, February 1995 (Electrotech Ltd.)
J.B.	S. McClatchie et al., "300 mm arriving fast," Abstract from European Semiconductor, Vol. 17, No. 8, November 1995.
J.B.	S. McClatchie et al., "Low Dielectric Constant Flowfill® Technology For IMD Applications," Electrotech Ltd. Brochure (date unknown).
J.B.	Ralls et al., <u>Introduction to Materials Science and Engineering</u> , John Wiley & Sons, Inc. 1976, pp. 312-313.
J.B.	P. Singer, "New Interconnect Materials: Chasing the Promise of Faster Chips," Semiconductor International, November 1994, pp. 52-56.
J.B.	"Silanol Terminated And Related Polydimethylsiloxanes," United Chemical Technologies, Inc., website: unitedchem.com/silanol.html , last updated 8/11/98.
J.B.	"Silane Coupling Agent Chemistry," United Chemical Technologies, Inc., website: unitedchem.com/coupling.html , last updated 8/11/98.
J.B.	"Parylene Conformal Coatings," Para Tech Coating, Inc. © 1996

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